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② Drafts

③ Pending

④ Active

- ⑤ L1: (82) (fin adj field adj effect adj transistor) or finfet
- ⑤ L2: (32) 1 and trench\$2
- ⑤ L3: (25) 2 and (grow\$3 or regrow\$3)
- ⑤ L4: (4) 2 and trench\$2.clm.
- ⑤ L5: (13) 1 and (trench\$2 or hole\$1 or via\$1).sim

⑥ Failed

⑦ Saved

⑧ (0) ("(thinadjfilm)nearresistor").PN.

⑨ (0) ("(thinadjfilm)nearresistor").PN.

⑩ (150130) thin adj film

⑪ (14857) (thin adj film) and resistor

⑫ (2054) ((thin adj film) and resistor) and ((thin adj film) n

⑬ (1735) (((thin adj film) and resistor) and ((thin adj film) i

⑭ (801) (((thin adj film) and resistor) and ((thin adj film) i

⑮ (499) (((thin adj film) and resistor) and ((thin adj film) i

⑯ (124) (((thin adj film) and resistor) and ((thin adj film) i

⑰ (34) (((thin adj film) and resistor) and ((thin adj film) i

⑱ (98) (((thin adj film) and resistor) and ((thin adj film) i

⑲ Favorites

U	P	I	Document ID	Issue Date	Paged	Title	Current EP	Current EP	EP Int'l level	Inventor	S	C	R	F	E	M	
3	Γ	Γ	Γ	US	20040311	16	Method of forming an N	438/154									
					20040048424		channel and P channel F										
4	Γ	Γ	Γ	US	20040311	23	Semiconductor device	257/500									
					20040046227												
5	Γ	Γ	Γ	US	20040226	48	Concurrent Fin-FET and	257/347									
					20040035118		thick-body device fabri										
6	Γ	Γ	Γ	US	20030731	13	Fin-type resistors	257/536	257/375;								
					20030141569			257/E21.00									
7	Γ	Γ	Γ	US	6720231	20040413	13	Fin-type resistors	438/382	257/722;							
					B2			438/238;									
8	Γ	Γ	Γ	US	6709982	20040323	12	Double spacer FinFET	438/696	438/304;							
					B1		formation	438/596									
9	Γ	Γ	Γ	US	6706571	20040316	15	Method for forming	438/157	438/283;							
					B1		multilink structures in	438/286;									
10	Γ	Γ	Γ	US	6580137	20030617	33	Damascene double-gated	257/401	257/407;							
					B2		transistors and related	257/E21.40									
11	Γ	Γ	Γ	US	6525403	20030225	20	Semiconductor device	257/618	257/329;							
					B2		having MIS field effect	257/330;									
12	Γ	Γ	Γ	US	6521502	20030218	8	Solid phase epitaxy	438/305	438/528							
					B1		activation process for										
13	Γ	Γ	Γ	US	6403434	20020611	10	Process for	438/300	257/E21.16							
					B1		manufacturing MO ₂ trans	61									

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